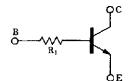


COMPOUND TRANSISTOR AA1L4Z

on-chip resistor NPN silicon epitaxial transistor For mid-speed switching

FEATURES

 On-chip bias resistor (R₁ = 47 kΩ)



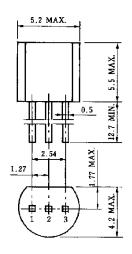
· Complementary transistor with AN1L4Z

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Ratings	Unit	
Collector to base voltage	Vcво	60	V	
Collector to emitter voltage	VCEO	50	V	
Emitter to base voltage	V _{EBO}	5	V	
Collector current (DC)	Ic(DC)	100	mA	
Collector current (Pulse)	Ic(pulse) *	200	mA	
Total power dissipation	Рт	250	mW	
Junction temperature	Tj	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

^{*} PW \leq 10 ms, duty cycle \leq 50 %

PACKAGE DRAWING (UNIT: mm)



Electrode Connection

Emitter EIAJ : SC-43B
 Collector JEDEC : TO-92
 Base IEC : PA33

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	V _{CB} = 50 V, I _E = 0			100	nA
DC current gain	h _{FE1} **	VcE = 5.0 V, Ic = 5.0 mA	135	270	600	-
DC current gain	h _{FE2} **	VcE = 5.0 V, Ic = 50 mA	100	260		-
Collector saturation voltage	V _{CE(sat)} **	Ic = 5.0 mA, I _B = 0.25 mA		0.05	0.2	V
Low level input voltage	VIL **	$V_{CE} = 5.0 \text{ V}, \text{ Ic} = 100 \ \mu\text{A}$		0.57	0.5	V
High level input voltage	V _{IH} **	VcE = 0.2 V, Ic = 5.0 mA	4.0	1.7		V
Input resistance	R ₁		32.9	47	61.1	kΩ
Turn-on time	ton	V cc = 5.0 V , R L = 1.0 $k\Omega$			0.2	μs
Storage time	t stg	$V_1 = 5.0 \text{ V}, \text{ PW} = 2.0 \ \mu\text{s}$			5.0	μs
Turn-off time	toff	duty cycle≤2 %			6.0	μs

^{**} Pulse test PW \leq 350 μ s, duty cycle \leq 2 %

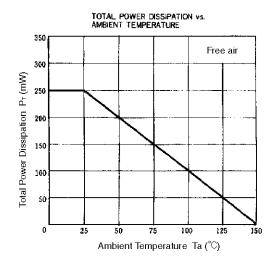
hfe CLASSIFICATION

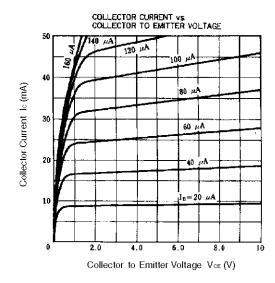
Marking	Q	Р	К
h _{FE1}	135 to 270	200 to 400	300 to 600

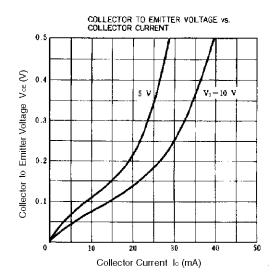
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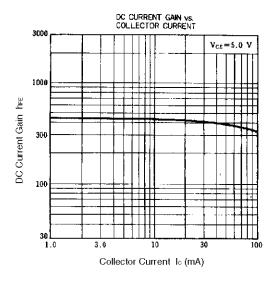


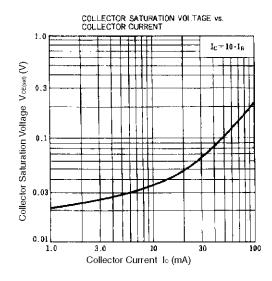
TYPICAL CHARACTERISTICS (Ta = 25°C)

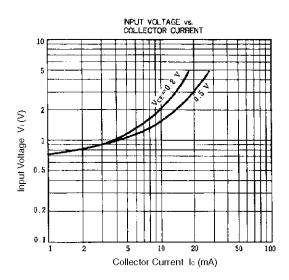


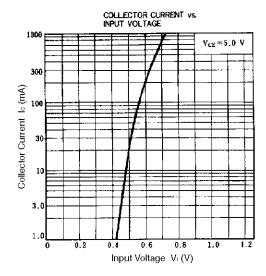


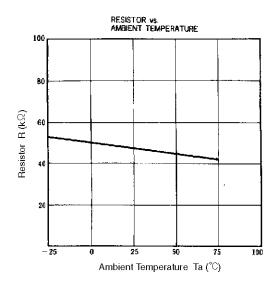












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